查询"2SK376份供应商Field Effect Transistor Silicon N Channel MOS Type (兀MOS)

2SK3761

unit: mm

Switching Regulator Applications

- Low drain-source ON resistance: RDS (ON) = 0.9 (typ.)
- High forward transfer admittance: $|Y_{fs}| = 5.0S$ (typ.)
- Low leakage current: $IDSS = 100 \mu A (VDS = 600 V)$
- Enhancement-mode: $V_{th} = 2.0 \sim 4.0 \text{ V}$ ($V_{DS} = 10 \text{ V}$, $I_{D} = 1 \text{ mA}$)

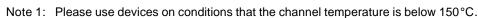
Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V_{DSS}	600	V	
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)		V_{DGR}	600	V	
Gate-source voltage		V_{GSS}	±30	V	
Drain current	DC (Note 1)	l _D	6	Α	
	Pulse (t = 1 ms) (Note 1)	l _{DP}	24		
Drain power dissipation (Tc = 25°C)		P_{D}	74	W	
Single pulse avalanche energy (Note 2)		E _{AS}	54	mJ	
Avalanche current		l _{AR}	6	Α	
Repetitive avalanche energy (Note 3)		E _{AR}	7.4	mJ	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	

Weight : 2.0g(typ.)

Thermal Characteristics

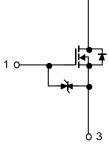
Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R _{th (ch-c)}	1.68	°C/W
Thermal resistance, channel to ambient	R _{th (ch-a)}	83.3	°C/W



Note 2: $V_{DD} = 90 \text{ V}$, $T_{ch} = 25^{\circ}\text{C}$ (initial), L = 2.6 mH, $I_{AR} = 6 \text{ A}$, $R_G = 25 \Omega$

Note 3: Repetitive rating: Pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device. Please handle with caution.



φ2



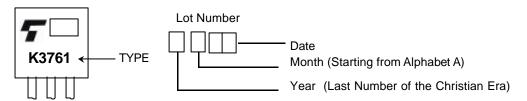
Erectrica β Character istics (Ta = 25°C)

Char	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		lgss	$V_{GS} = \pm 25 V, V_{DS} = 0 V$	_	_	±10	μΑ
Gate-source breakdown voltage		V (BR) GSS	$I_D = \pm 10 \ \mu A, \ V_{GS} = 0 \ V$	±30	_	_	V
Drain cut-off curi	Drain cut-off current		$V_{DS} = 600 \text{ V}, V_{GS} = 0 \text{ V}$	_	_	100	μΑ
Drain-source bre	akdown voltage	V (BR) DSS	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	600	_	_	V
Gate threshold v	oltage	V_{th}	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$	2.0	_	4.0	V
Drain-source ON	l resistance	R _{DS (ON)}	$V_{GS} = 10 \text{ V}, I_D = 3 \text{ A}$	_	0.9	1.25	Ω
Forward transfer	admittance	Y _{fs}	$V_{DS} = 10 \text{ V}, I_D = 3 \text{ A}$	1.2	5.0	_	S
Input capacitance		C _{iss}	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz	_	1050	_	pF
Reverse transfer capacitance		C _{rss}		_	10	_	
Output capacitance		C _{oss}]	_	110	_	
Switching time	Rise time	t _r	V_{GS} V_{OUT} V_{GS} $V_{DD} \simeq 200 V$	_	20		
	Turn-on time	t _{on}		_	40	_	
	Fall time	t _f			35		ns
	Turn-off time	t _{off}	Duty ≤ 1%, t _w = 10 μs	_	130		
Total gate charge		Qg		_	28	_	
Gate-source charge		Q _{gs}	$V_{DD} \simeq 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 6 \text{ A}$	_	16	_	nC
Gate-drain charge		Q _{gd}]		12	_	

Source-Drain Ratings and Characteristics (Ta = 25°C)

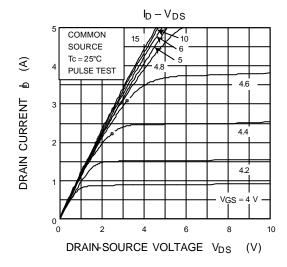
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	l _{DR}	_	_	_	6	Α
Pulse drain reverse current (Note 1)	I _{DRP}	_	_	_	24	Α
Forward voltage (diode)	V_{DSF}	$I_{DR} = 6 \text{ A}, V_{GS} = 0 \text{ V}$	_	_	-1.7	V
Reverse recovery time	t _{rr}	$I_{DR} = 6 A, V_{GS} = 0 V,$		1000	_	ns
Reverse recovery charge	Q _{rr}	$dI_{DR}/dt = 100 A/\mu s$		7	_	μС

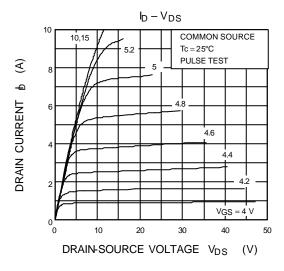
Marking

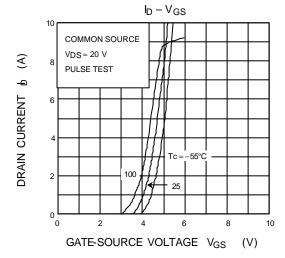


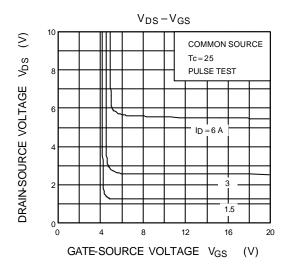
2 2004-02-26

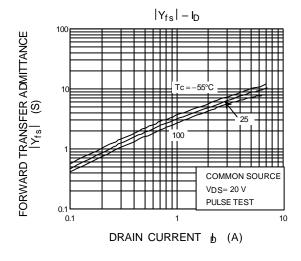
查询"2SK3761"供应商

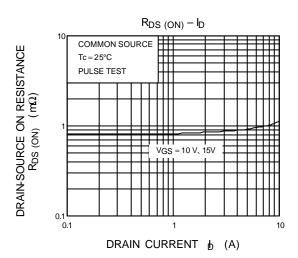






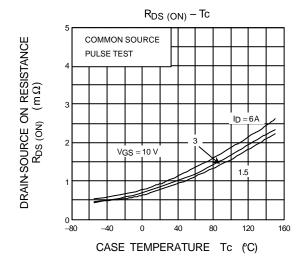


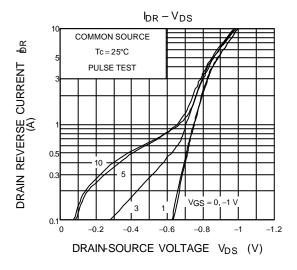




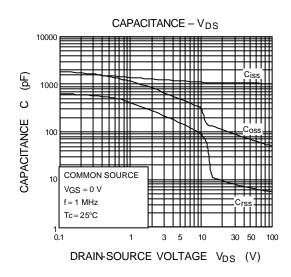


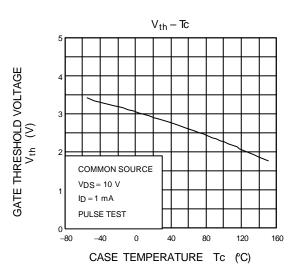
查询"28K3761"供应商

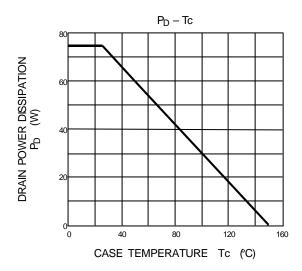


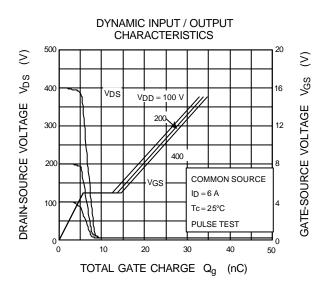


2SK3761

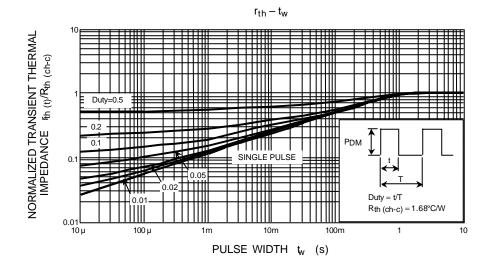


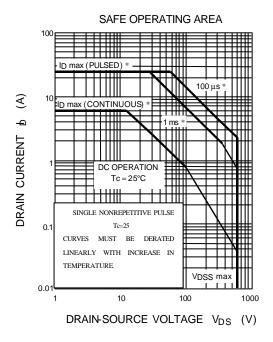


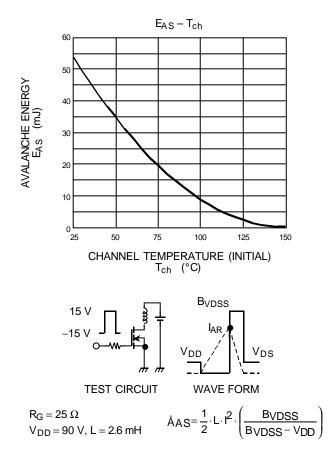




查询"2SK3761"供应商







查询"2SK3761"供应商

RESTRICTIONS ON PRODUCT USE

Handbook" etc..

030619EAA

- The information contained herein is subject to change without notice.
- The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA for any infringements of patents or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of TOSHIBA or others.
- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in this document shall be made at the customer's own risk.
- TOSHIBA products should not be embedded to the downstream products which are prohibited to be produced and sold, under any law and regulations.